Form 1449*	Atty. Docket No.: 303.678US4	Serial No. Unknown
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U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes	No

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Examiner PHUC T. DANG	Date Considered 11/25/2002

*Substitute Disclosure Statement Form (PTO-1449)

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